

# **isc Silicon PNP Power Transistors**

#### **DESCRIPTION**

- · Low Saturation Voltage
- Good Linearity of hFE
- · Fast Switching Speeds
- Complement to Type D44C3
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

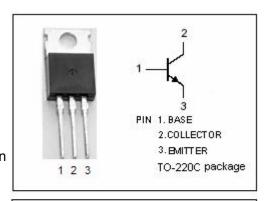
 Designed for various specific and general purpose application such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0MHz series, shunt and switching regulators; low and high frequency inverters/ converters and many others.

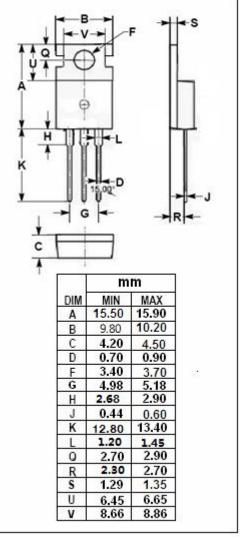
# ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector-Emitter Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current-Continuous	-4	Α
I <sub>CM</sub>	Collector Current-Peak	-6	Α
lΒ	Base Current-Continuous	-1	Α
Pc	Collector Power Dissipation @Tc=25°C	30	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	4.2	°C/W







# isc Silicon PNP Power Transistors

**D45C3** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

10-20 C um	16-23 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -50mA			-0.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -100mA			-1.3	V			
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = -40V, V <sub>BE</sub> = 0			-10	μА			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	μА			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.2A; V <sub>CE</sub> = -1V	40		120				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -1V	20						
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -20mA;V <sub>CE</sub> = -4V;f <sub>test</sub> = 1MHz		40		MHz			
Switching Times									
t <sub>r</sub>	Rise Time				0.2	μS			
ts	Storage Time	I <sub>C</sub> = -1A; I <sub>B1</sub> = -I <sub>B2</sub> = -0.1A; V <sub>CC</sub> = -20V			0.6	μS			
t <sub>f</sub>	Fall Time				0.3	μs			

#### **NOTICE:**

isc website: www.iscsemi.cn

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